

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. PIS920030377		SERIAL NO.	
				Huang et al.			
				FILING		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
SJL	2002/0081520	06-27-02	Sooriyakumaran et al.	430	270.1		
	2001/0036594	11-01-01	Kozawa et al.	430	270.1		
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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
SJL		"Effects of resist components on image spreading during postexposure bake of chemically amplified resists", Hinsberg et al. Proceedings of SPIE Vol. 3999 (2000), ppgs. 148-160					
SJL		"Determination of coupled acid catalysis-diffusion processes in a positive-tone chemically amplified photoresist" Houle et al. Journal Vac. Sci. Technology B 18 (4) Jul/Aug 2000, ppgs. 1874-1885					
SJL		"Direct measurement of the reaction front in chemically amplified photoresists" Lin et al. Science, Vol. 297, 19 July 2002, ppgs. 372-375					
SJL		"Modeling and simulations of a positive chemically amplified photoresist for ex-ray lithography", Krasnoper va et al., Journal Vac. Sci. Technology B 12 (6) Nov/Dec 1994, ppgs. 3900-3904					
EXAMINER <i>Si H. Lu</i>			DATE CONSIDERED 3/2/'05				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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SJL	Appl. no. 10/604,082, FIS9-2003-0154US1 "Process for forming features of 50 nm or less half-pitch with chemically amplified resist imaging" Medeiros et al., Filed 06-25-03

EXAMINER

S. J. Lee

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3/2/05

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